

# **BAP50-03**

# **General purpose PIN diode**

# FEATURES

- Low diode capacitance
- Low diode forward resistance.

## APPLICATIONS

• General RF applications.

## DESCRIPTION

General purpose PIN diode in a SOD323 small plastic SMD package.

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	50	V
IF	continuous forward current		_	50	mA
P <sub>tot</sub>	total power dissipation	T <sub>s</sub> = 90 °C	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

## ELECTRICAL CHARACTERISTICS

 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

SYMBOL	PARAMETER	AMETER CONDITIONS				UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 50 mA	-	0.95	1.1	V
V <sub>R</sub>	reverse voltage	I <sub>R</sub> = 10 μA	50	-	—	V
I <sub>R</sub>	reverse current	-	-	100	nA	
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 0; f = 1 MHz	-	0.4	-	pF
		V <sub>R</sub> = 1 V; f = 1 MHz	-	0.3	0.55	pF
		V <sub>R</sub> = 5 V; f = 1 MHz	-	0.2	0.35	pF
r <sub>D</sub>	diode forward resistance	I <sub>F</sub> = 0.5 mA; f = 100 MHz; note 1	-	25	40	Ω
		I <sub>F</sub> = 1 mA; f = 100 MHz; note 1	-	14	25	Ω
		I <sub>F</sub> = 10 mA; f = 100 MHz; note 1	-	3	5	Ω

#### Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-s</sub>	thermal resistance from junction to soldering point	85	K/W





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## **GRAPHICAL DATA**



f = 100 MHz; T<sub>j</sub> = 25 °C.

Fig.2 Forward resistance as a function of forward current; typical values.



(1)  $I_F = 10 \text{ mA.}$  (2)  $I_F = 1 \text{ mA.}$  (3)  $I_F = 0.5 \text{ mA.}$ 

Diode inserted in series with a 50  $\Omega$  stripline circuit and biased via the analyzer Tee network.  $T_{amb}$  = 25 °C.

Fig.4 Insertion loss  $(|S_{21}|^2)$  of the diode as a function of frequency; typical values.



f = 1 MHz; T<sub>j</sub> = 25 °C.

Fig.3 Diode capacitance as a function of reverse voltage; typical values.



Diode zero biased and inserted in series with a 50  $\Omega$  stripline circuit. T<sub>amb</sub> = 25 °C.

Fig.5 Isolation  $(|S_{21}|^2)$  of the diode as a function of frequency; typical values.



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PACKAGE OUTLINE

# Plastic surface mounted package; 2 leads







0 1 2 mm

DIMENSIONS (mm are the original dimensions)										
UNIT	A	A <sub>1</sub>	ь <sub>р</sub>	с	D	Е	Η <sub>E</sub>	Lp	v	
mm	1.0 	0.10 - 0.00	0.35 0.25	0.15 0.08	1.8 1.6	1.40 1.20	2.7 2.5	0.40 0.25	0.90 0.80	

Note

1. The marking bar indicates the cathode.





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